

SCCS063A - June 1997 - Revised April 2000

16-Bit Latched Transceiver

CY74FCT163543

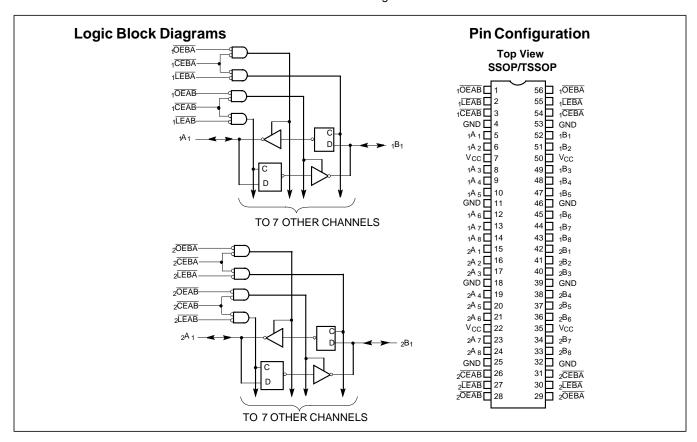
Features

- Low power, pin-compatible replacement for LCX and LPT families
- · 5V tolerant inputs and outputs
- · 24 mA balanced drive outputs
- · Power-off disable outputs permits live insertion
- Edge-rate control circuitry for reduced noise
- FCT-C speed at 5.1 ns
- Latch-up performance exceeds JEDEC standard no. 17
- ESD > 2000V per MIL-STD-883D, Method 3015
- Typical output skew < 250 ps
- Industrial temperature range of -40°C to +85°C
- TSSOP (19.6-mil pitch) or SSOP (25-mil pitch)
- Typical V_{olp} (ground bounce) performance exceeds Mil Std 883D
- V_{CC} = 2.7V to 3.6V

Functional Description

The CY74FCT163543 is a 16-bit, high-speed, low power latched transceiver that is organized as two independent 8-bit D-type latched transceivers, containing two sets of eight D-type latches with separate Latch Enable ($\overline{\text{LEAB}}$, $\overline{\text{LEAB}}$) and Output Enable ($\overline{\text{OEAB}}$, $\overline{\text{OEAB}}$) controls for each set to permit independent control of inputting and outputting in either direction of data flow. For data flow from A to B, for example, the A-to-B input Enable ($\overline{\text{CEAB}}$) must be LOW in order to enter data from A or to take data from B, as indicated in the truth table. With $\overline{\text{CAEB}}$ LOW, a LOW signal on the A-to-B Latch Enable ($\overline{\text{LEAB}}$) makes the A-to-B latches transparent; a subsequent LOW-to-HIGH transition of the $\overline{\text{LEAB}}$ signal puts the A latches in the storage mode and their outputs no longer follow the A inputs. With $\overline{\text{CEAB}}$ and $\overline{\text{OEAB}}$ both LOW, the three-state B output buffers are active and reflect the data present at the output of the A latches. Control of data from B to A is similar, but uses $\overline{\text{CEAB}}$, $\overline{\text{LEAB}}$, and $\overline{\text{OEAB}}$ inputs.

The CY74FCT163543 has 24-mA balanced output drivers with current limiting resistors in the outputs. This reduces the need for external terminating resistors and provides for minimal undershoot and reduced ground bounce. The inputs and outputs are capable of being driven by 5.0V buses, allowing them to be used in mixed voltage systems as translators. The outputs are also designed with a power off disable feature enabling them to be used in applications requiring live insertion. Flow-through pinout and small shrink packaging simplify board design.





Pin Description

Name	Description
OEAB	A-to-B Output Enable Input (Active LOW)
OEBA	B-to-A Output Enable Input (Active LOW)
CEAB	A-to-B Enable Input (Active LOW)
CEBA	B-to-A Enable Input (Active LOW)
LEAB	A-to-B Latch Enable Input (Active LOW)
LEBA	B-to-A Latch Enable Input (Active LOW)
Α	A-to-B Data Inputs or B-to-A Three-State Outputs
В	B-to-A Data Inputs or A-to-B Three-State Outputs

Maximum Ratings^[3, 4]

(Above which the useful life may be impaired. For user guidelines, not tested.)
Storage Temperature55°C to +125°C
Ambient Temperature with Power Applied –55°C to +125°C
Supply Voltage Range
DC Input Voltage0.5V to +7.0V
DC Output Voltage0.5V to +7.0V
DC Output Current (Maximum Sink Current/Pin)60 to +120 mA

Function Table^[1]

	Inputs		Latch Status	Output Buffers
CEAB	LEAB	OEAB	A to B	В
Н	Х	Х	Storing	High Z
Х	Н	Х	Storing	X
Х	Х	Н	Х	High Z
L	L	L	Transparent	Current A Inputs
L	Н	L	Storing	Previous A Inputs ^[2]

Power Dissipation	1.0W
Static Discharge Voltage	>2001V
(per MIL-STD-883, Method 3015)	

Operating Range

Range	Ambient Temperature	V _{CC}
Industrial	-40°C to +85°C	2.7V to 3.6V



Electrical Characteristics Over the Operating Range V_{CC}=2.7V to 3.6V

Parameter	Description	Test	Conditions	Min.	Typ. ^[5]	Max.	Unit
V _{IH}	Input HIGH Voltage			2.0		5.5	V
V _{IL}	Input LOW Voltage					0.8	V
V _H	Input Hysteresis ^[6]				100		mV
V _{IK}	Input Clamp Diode Voltage	V _{CC} =Min.,	I _{IN} =-18 mA		-0.7	-1.2	V
I _{IH}	Input HIGH Current	V _{CC} =Max.,	V _{CC} =5.5V			<u>+</u> 1	μΑ
I _{IL}	Input LOW Current	V _{CC} =Max.,	V _{CC} =GND			<u>+</u> 1	μΑ
I _{OZH}	High Impedance Output Current (Three-State pins)	V _{CC} =Max.,	V _{OUT} =5.5V			<u>+</u> 1	μΑ
I _{OZL}	High Impedance Output Current (Three-State pins)	V _{CC} =Max.,	V _{OUT} =GND			<u>+</u> 1	μΑ
I _{ODL}	Output LOW Current ^[7]	V _{CC} =3.3V, V _{OUT} =1.5V	$V_{IN}=V_{IH}$ or V_{IL} ,	50	90	200	mA
I _{ODH}	Output HIGH Current ^[7]	V _{CC} =3.3V, V _{OUT} =1.5V	$V_{IN}=V_{IH}$ or V_{IL} ,	-36	-60	-110	mA
V _{OH}	Output HIGH Voltage	V _{CC} =Min.,	I _{OH} =-0.1 mA	V _{CC} -0.2			V
		V _{CC} =3.0V,	I _{OH} =-8 mA	2.4	3.0		
		V _{CC} =3.0V,	I _{OH} =-24 mA	2.0	3.0		
V _{OL}	Output LOW Voltage	V _{CC} =Min.,	I _{OL} =0.1mA			0.2	V
		V _{CC} =Min.,	I _{OL} =24mA		3.0	0.5	
I _{OS}	Short Circuit Current ^[7]	V _{CC} =Max.,	V _{OUT} =GND	-60	-135	-240	mA
I _{OFF}	Power-Off Disable	V _{CC} =0V,	V _{OUT} ≤4.5V			<u>+</u> 100	μΑ

A-to-B data flow shown; B-to-A flow control is the same, except using CEBA, LEBA, and OEBA.

Data prior to LEAB LOW-to-HIGH Transition H = HIGH Voltage Level. L = LOW Voltage Level. X = Don't Care. Z = High Impedance.

Operation beyond the limits set forth may impair the useful life of the device. Unless noted, these limits are over the operating free-air temperature range. Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.

Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground. Typical values are at V_{CC} = 3.3V, T_A = +25°C ambient. This parameter is specified but not tested. Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

Capacitance^[6] ($T_A = +25$ °C, f = 1.0 MHz)

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	4.5	6.0	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	5.5	8.0	pF



Power Supply Characteristics

Parameter	Description	Test Conditions		Typ. ^[5]	Max.	Unit
I _{CC}	Quiescent Power Supply Current	V _{CC} =Max.	V _{IN} ≤0.2V, V _{IN} ≥V _{CC} −0.2V	0.1	10	μΑ
Δl _{CC}	Quiescent Power Supply Current (TTL inputs HIGH)	V _{CC} =Max.	V _{IN} =V _{CC} -0.6V ^[8]	2.0	30	μΑ
I _{CCD}	Dynamic Power Supply Current ^[9]	V _{CC} =Max., One Input Toggling, 50% <u>Duty</u> Cycle, Outputs Open, OE =GND	V _{IN} =V _{CC} or V _{IN} =GND	50	75	μA/MHz
I _C	Total Power Supply Current ^[10]	V _{CC} =Max., f ₁ =10 MHz, 50% Duty Cycle, Outputs	V _{IN} =V _{CC} or V _{IN} =GND	0.5	0.8	mA
		Open, One Bit Toggling, OE=GND	V _{IN} =V _{CC} -0.6V or V _{IN} =GND	0.5	0.8	mA
		V _{CC} =Max., f ₁ =2.5 MHz, 50% Duty Cycle, Outputs	V _{IN} =V _{CC} or V _{IN} =GND	2.0	3.0 ^[11]	mA
		Open, Sixteen Bits Toggling, OE=GND	V _{IN} =V _{CC} -0.6V or V _{IN} =GND	2.0	3.3 ^[11]	mA

Switching Characteristics Over the Operating Range $V_{CC} = 3.0V$ to $3.6V^{[12,15]}$

		CY74FCT	163543A	CY74FCT	163543C		
Parameter	Description	Min.	Max.	Min.	Max.	Unit	Fig. No. ^[13]
t _{PLH} t _{PHL}	Propagation Delay, Transparent Mode A to B or B to A	1.5	6.5	1.5	5.1	ns	1, 3
t _{PLH} t _{PHL}	Propagation Delay LEBA to A, LEAB to B	1.5	8.0	1.5	5.6	ns	1, 5
t _{PZH} t _{PZL}	Output Enable Time OEBA or OEAB to A or B CEBA or CEAB to A or B	1.5	9.0	1.5	7.8	ns	1, 7, 8
t _{PHZ} t _{PLZ}	Output Disable Time OEBA or OEAB to A or B CEBA or CEAB to A or B	1.5	7.5	1.5	6.5	ns	1, 7, 8
t _{SU}	Set-up Time HIGH or LOW A or B to LEAB or LEBA	2.0	_	2.0	_	ns	4
t _H	Hold Time HIGH or LOW A or B to LEAB or LEBA	2.0	_	2.0	_	ns	4
t _W	LEBA or LEAB Pulse Width LOW	4.0	_	4.0	_	ns	5
t _{SK(O)}	Output Skew ^[14]	_	0.5	_	0.5	ns	_

Notes:

Per TTL driven input; all other inputs at V_{CC} or GND.

This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

= I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}
I_C = I_{CC}+ΔI_{CC}D_HN_T+I_{CCD}(f₀N_C/2 + f₁N₁)
I_{CC} = Quiescent Current with CMOS input levels
ΔI_{CC} = Power Supply Current for a TTL HIGH input (V_{IN}=3.4V)

 $I_{CC} = I_{CC} = \Delta I_{CC} = I_{CC} =$ Duty Cycle for TTL inputs HIGH Number of TTL inputs at DH

Dynamic Current caused by an input transition pair (HLH or LHL)

 $I_{CCD} = f_0 = N_C =$ Clock frequency for registered devices, otherwise zero

Number of clock inputs changing at f₁

Input signal frequency

= Number of inputs changing at f₁

All currents are in milliamps and all frequencies are in megahertz.

11. Values for these conditions are examples of the I_{CC} formula. These limits are specified but not tested.

12. Minimum limits are specified but not tested on Propagation Delays.

13. See "Parameter Measurement Information" in the General Information section.

14. Skew between any two outputs of the same package switching in the same directional. This parameter is ensured by design.

15. For V_{CC} =2.7, propagation delay, output enable and output disable times should be degraded by 20%.

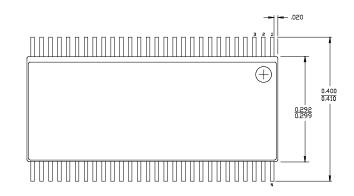


Ordering Information CY74FCT163543

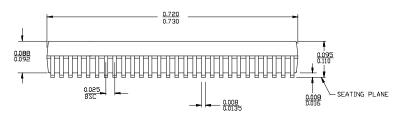
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
5.1	CY74FCT163543CPACT	Z56	56-Lead (240-Mil) TSSOP	Industrial
	CY74FCT163543CPVC/PVCT	O56	56-Lead (300-Mil) SSOP	7
6.5	CY74FCT163543APVC/PVCT	O56	56-Lead (300-Mil) SSOP	Industrial

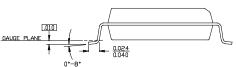
Package Diagrams

56-Lead Shrunk Small Outline Package O56



DIMENSIONS IN INCHES MIN. MAX.

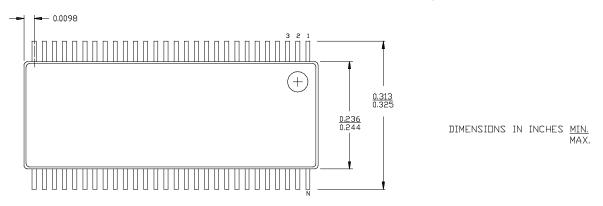


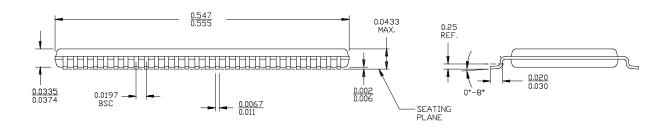




Package Diagrams (continued)

56-Lead Thin Shrunk Small Outline Package Z56





IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgment, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Customers are responsible for their applications using TI components.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 2000, Texas Instruments Incorporated